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	(CLARK-PR & CI						iai wale		De sile
Customer C	•	PCN Manac				ept:		Oua	lity Service
	st Ship Date:	Jun 22, 20	2 2023 Sample					-	22, 2023*
*Sample re	quests receive	ed after Jar	nuarv 22		-			ed.	
Change Typ	-			/					
Assemb			Design				Wafer	Bum	p Site
	ly Process		Data Sh	eet					p Material
Assemb	ly Materials		Part nur	nber cha	nge		Wafer	Bum	p Process
Mechani	ical Specificatio	n 🛛	Test Site	e			Wafer	Fab	Site
Packing/	/Shipping/Label	ing	Test Pro	cess		\square	Wafer	Fab	Materials
							Wafer	Fab	Process
			PCN D	etails					
Description	of Change:								
<mark>TLC59116ITF</mark> The device a Texas Instru	PWTQ1 under G iffected is highlig ments is please	roup 1 devic ghted and b d to annound	e that w olded ur ce the qu	<mark>as not in</mark> nder Grou ualificatio	ncluded o up 4 in t on of its	on the he de: RFAB	origina vice list fabrica	<mark>al PCN</mark> t belo ition f	N notifications ow. facility as a
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TLC59116ITF The device a Texas Instru additional Wa the selected Current Fa Site MIHO	PWTQ1 under G affected is highlight ments is please afer Fab source devices listed ir Current Fab ab Process LBC7 hanges are as for vices: DL-MOS vices:	roup 1 devic ghted and b d to annound and CLARK- n the "Produc Site s Wa Dian 200 ollows: be Site	e that woolded un ce the qu PR and C ct Affecto ofer mm	as not in nder Grou DAT-PR ed" section Additi Fab s RF/ W Probe CLARK-P	icluded of up 4 in t on of its as an a on. A ional Site AB	n the he de RFAB dditio dditic	fabrica nal prol	t belo tion f be sit	A notification ow. facility as a ce options f ce Wafer Diamete
TLC59116ITH The device a Texas Instru additional Wa the selected Current Fa Site MIHO Probe site ch Group 2 De	PWTQ1 under G affected is highlight ments is please afer Fab source devices listed ir Current Fab ab Process LBC7 hanges are as for vices: Current Pro DL-MOS vices:	roup 1 devic ghted and b d to annound and CLARK- the "Produce Site S Wa Dian 200 ollows: be Site 5 -4	e that woolded un ce the qu PR and C ct Affecto ofer mm	as not in nder Grou DAT-PR ed" section Additi Fab s RFA	icluded of up 4 in t on of its as an a on. A ional Site AB	n the he de RFAB dditio dditic	fabrica nal prol	t belo tion f be sit	A notification ow. facility as a ce options f ce Wafer Diamete
TLC59116ITH The device a Texas Instru additional Wa the selected Current Fa Site MIHO Probe site ch Group 2 De	PWTQ1 under G affected is highlight ments is please afer Fab source devices listed ir Current Fab ab Process LBC7 hanges are as for vices: DL-MOS vices:	roup 1 devic ghted and b d to annound and CLARK- n the "Produc Site s Wa Dian 200 ollows: be Site 5-4	e that woolded un ce the qu PR and C ct Affecto ofer mm	as not in nder Grou DAT-PR ed" section Additi Fab s RF/ W Probe CLARK-P	icluded of up 4 in t on of its as an a on. A ional Site AB	n the he de RFAB dditio dditic	fabrica nal prol	t belo tion f be sit	A notification ow. facility as a ce options f ce Wafer Diamete

Group 4 Devices:

Current Probe Site	New Probe Site
MH8	DL-MOS-4

Test coverage, insertions, conditions will remain consistent with current testing.

Reason for Change:

Continuity of Supply

Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative): None

Changes to product identification resulting from this PCN:

Chip Site	Chip Site Origin Code (20L)	Chip Site Country Coc (21L)	de Chip Site City	
MIHO8	MH8	JPN	Ibaraki	
RFAB	RFB	USA	Richardson	
TEXAS INSTRUMENTS MADE IN: Malaysia 2DC: 20: MSL 2 /260C/1 YEAR SE	/29/04 06 3 3 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4	(1P) SN74LSO7N (Q) 2000 (1 (31T) LOT: 3959 (4W) TKY (1T) 75 (P) (20L) CSO: SHEV (21	D) 0336 047MLA 523483512	
		(22L) AS0: MLA (23	L) ACO. MIS	
roduct Affected:				
roup 1 device list - M	IIHO adding RFAB as a			
roup 1 device list - M 5N2002036QRTERQ1	TLC59116ITPWTQ1	TPS62260QDRVRMU	TPS62290IDRVRQ1	
r oup 1 device list - M SN2002036QRTERQ1 SN55340QRTERQ1	TLC59116ITPWTQ1 TPD3S716QDBQRQ1	TPS62260QDRVRMUTPS62260TDDCRQ1	TPS62290TDRVRQ1	
roup 1 device list - M SN2002036QRTERQ1 SN55340QRTERQ1 SN55340QRTETQ1	TLC59116ITPWTQ1TPD3S716QDBQRQ1TPS55340QRTERQ1	TPS62260QDRVRMUTPS62260TDDCRQ1TPS62260TDRVRQ1	TPS62290TDRVRQ1 TPS62293TDRVRQ1	
roup 1 device list - M SN2002036QRTERQ1 SN55340QRTERQ1 SN55340QRTETQ1	TLC59116ITPWTQ1 TPD3S716QDBQRQ1	TPS62260QDRVRMUTPS62260TDDCRQ1	TPS62290TDRVRQ1	
roup 1 device list - M SN2002036QRTERQ1 SN55340QRTERQ1 SN55340QRTETQ1 FAS6422QDKQQ1	TLC59116ITPWTQ1TPD3S716QDBQRQ1TPS55340QRTERQ1	TPS62260QDRVRMUTPS62260TDDCRQ1TPS62260TDRVRQ1	TPS62290TDRVRQ1 TPS62293TDRVRQ1	
roup 1 device list - M 5N2002036QRTERQ1 5N55340QRTERQ1 5N55340QRTETQ1 FAS6422QDKQQ1 FAS6422QDKQRQ1	TLC59116ITPWTQ1TPD3S716QDBQRQ1TPS55340QRTERQ1TPS55340QRTERWB	TPS62260QDRVRMUTPS62260TDDCRQ1TPS62260TDRVRQ1TPS62261TDRVRQ1	TPS62290TDRVRQ1 TPS62293TDRVRQ1	
roup 1 device list - M SN2002036QRTERQ1 SN55340QRTERQ1 SN55340QRTETQ1 TAS6422QDKQQ1 TAS6422QDKQRQ1 TLC59116ITPWRQ1 roup 2 device list - M	TLC59116ITPWTQ1TPD3S716QDBQRQ1TPS55340QRTERQ1TPS55340QRTERWBTPS55340QRTETQ1TPS62260IDRVRQ1	TPS62260QDRVRMUTPS62260TDDCRQ1TPS62260TDRVRQ1TPS62261TDRVRQ1TPS62262TDRVRQ1TPS62263TDRVRQ1CLARK-PR Probe site	TPS62290TDRVRQ1 TPS62293TDRVRQ1 TPS62590TDRVRQ1	
roup 1 device list - N SN2002036QRTERQ1 SN55340QRTERQ1 SN55340QRTETQ1 FAS6422QDKQQ1 FAS6422QDKQRQ1 FLC59116ITPWRQ1 roup 2 device list - N FPA3110D2QPWPRQ1	TLC59116ITPWTQ1TPD3S716QDBQRQ1TPS55340QRTERQ1TPS55340QRTERWBTPS55340QRTETQ1TPS62260IDRVRQ1	TPS62260QDRVRMUTPS62260TDDCRQ1TPS62260TDRVRQ1TPS62261TDRVRQ1TPS62262TDRVRQ1TPS62263TDRVRQ1CLARK-PR Probe siteTPA3112D1QPWPRQ1	TPS62290TDRVRQ1 TPS62293TDRVRQ1 TPS62590TDRVRQ1	
roup 1 device list - M SN2002036QRTERQ1 SN55340QRTERQ1 SN55340QRTETQ1 FAS6422QDKQQ1 FAS6422QDKQRQ1 FLC59116ITPWRQ1 roup 2 device list - M FPA3110D2QPWPRQ1 roup 3 device list - M	TLC59116ITPWTQ1TPD3S716QDBQRQ1TPS55340QRTERQ1TPS55340QRTERWBTPS55340QRTETQ1TPS62260IDRVRQ1	TPS62260QDRVRMUTPS62260TDDCRQ1TPS62260TDRVRQ1TPS62261TDRVRQ1TPS62262TDRVRQ1TPS62263TDRVRQ1CLARK-PR Probe site:TPA3112D1QPWPRQ1CDAT-PR Probe site:	TPS62290TDRVRQ1 TPS62293TDRVRQ1 TPS62590TDRVRQ1	
roup 1 device list - N SN2002036QRTERQ1 SN55340QRTERQ1 SN55340QRTETQ1 TAS6422QDKQQ1 TAS6422QDKQRQ1 TLC59116ITPWRQ1 roup 2 device list - N TPA3110D2QPWPRQ1 roup 3 device list - N TPS54388CQRTERQ1	TLC59116ITPWTQ1TPD3S716QDBQRQ1TPS55340QRTERQ1TPS55340QRTERWBTPS55340QRTETQ1TPS62260IDRVRQ1IHO adding RFAB andTPA3111D1QPWPRQ1IHO adding RFAB andTPS54618CQRTERQ1	TPS62260QDRVRMUTPS62260TDDCRQ1TPS62260TDRVRQ1TPS62261TDRVRQ1TPS62262TDRVRQ1TPS62263TDRVRQ1CLARK-PR Probe site:TPA3112D1QPWPRQ1CDAT-PR Probe site:TPS57114CQRTERQ1	TPS62290TDRVRQ1 TPS62293TDRVRQ1 TPS62590TDRVRQ1	
roup 1 device list - M SN2002036QRTERQ1 SN55340QRTERQ1 SN55340QRTETQ1 FAS6422QDKQQ1 FAS6422QDKQRQ1 FLC59116ITPWRQ1 roup 2 device list - M FPA3110D2QPWPRQ1 roup 3 device list - M	TLC59116ITPWTQ1TPD3S716QDBQRQ1TPS55340QRTERQ1TPS55340QRTERWBTPS55340QRTETQ1TPS62260IDRVRQ1	TPS62260QDRVRMUTPS62260TDDCRQ1TPS62260TDRVRQ1TPS62261TDRVRQ1TPS62262TDRVRQ1TPS62263TDRVRQ1CLARK-PR Probe site:TPA3112D1QPWPRQ1CDAT-PR Probe site:	TPS62290TDRVRQ1 TPS62293TDRVRQ1 TPS62590TDRVRQ1	

Automotive New Product Qualification Summary (As per AEC-Q100 and JEDEC Guidelines)

Approved 17-Jun-2020

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Туре	#	Test Spec	Min Lot Qty	\$\$/Lot	Test Name / Condition	Duration	Qual Device: TA \$5441QPWPRQ1	QBS Process Reference: TPS2543QRTE
		Tes	t Group	A – Acce	lerated Environment Stress Tests			
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Automotive Preconditioning, L2	Level 2-260C	-	3/765/0
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Automotive Preconditioning, L3	Level 3-260C	3/1258/0	-
HAST	A2	JEDEC JESD22-A110	3	77	Biased HAST 130C/85%RH	96 Hours	3/231/0	3/240/0
AC	A3	JEDEC JESD22-A102	3	77	Auto Autoclave 121C	96 Hours	3/231/0	3/231/0
тс	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle, -65/150C, Grade-1	500 Cycles	3/231/0	3/231/0
TC-BP	A4	MIL-STD883 Method 2011	1	30	Post Temp. Cycle Bond Pull	500 Cycles	1/30/0	1/30/0
PTC	A5	JEDEC JESD22-A105	1	45	Power Temperature Cycle, -40/125C	1000 Cycles	1/45/0	1/45/0
HTSL	A6	JEDEC JESD22-A103	1	45	High Temp Storage Bake 175C	500 Hours	3/135/0	3/135/0
		Tes	st Group	B – Acce	lerated Lifetime Simulation Tests			
HTOL	B1	JEDEC JESD22-A108	3	77	Life Test, 125C	1000 Hours	3/231/0	-
HTOL	B1	JEDEC JESD22-A108	3	77	Life Test, 150C	408 Hours	-	3/231/0
ELFR	B2	AEC Q100-008	3	800	Early Life Failure Rate, 150C	24 Hours	-	3/2400/0
EDR	В3	AEC Q100-005	3	77	NVM Endurance, Data Retention, and Operational Life	-	N/A	-

		Test	Group	C – Pa	ackage Assembly Integrity Tests			
WBS	C1	AEC Q100-001	1	30	Wire Bond Shear (Cpk>1.67)	Wires	3/90/0	-
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull (Cpk>1.67)	Wires	3/90/0	-
SD	C3	JEDEC JESD22-B102	1	15	Surface Mount Solderability	Pb Free	1/15/0 (1)	2/30
SD	C3	JEDEC JESD22-B102	1	15	Surface Mount Solderability	Pb	1/15/0 (1)	-
PD	C4	JEDEC JESD22-B100 and B108	3	10	Auto Physical Dimensions	Cpk>1.67	3/30/0	3/30
LI	C6	JEDEC JESD22-B105	1	50	Lead Pull to Destruction	Leads	1/48/0	-
,		Tes	t Group) D – C	Die Fabrication Reliability Tests			
EM	D1	JESD61	-	-	Electromigration	-	Completed Per Process Technology Requirements	-
TDDB	D2	JESD35	-	-	Time Dependant Dielectric Breakdown	-	Completed Per Process Technology Requirements	-
нсі	D3	JESD60 & 28	-	-	Hot Injection Carrier	-	Completed Per Process Technology Requirements	-
NBTI	D4	-	-	-	Negative Bias Temperature Instability	-	Completed Per Process Technology Requirements	-
SM	D5	-	-	-	Stress Migration	-	Completed Per Process Technology Requirements	-
		т	est Gro	up E -	- Electrical Verification Tests		·	
нвм	E2	AEC Q100-002	1	3	ESD - HBM - Q100	1500 V	1/3/0	-
нвм	E2	AEC Q100-002	1	3	ESD - HBM - Q100	4000 V	-	1/3/
CDM	E3	AEC Q100-011	1	3	ESD - CDM - Q100	1000 V	1/3/0	-
CDM	E3	AEC Q100-011	1	3	ESD - CDM - Q100	1500 V	-	1/3/
LU	E4	AEC Q100-004	1	6	Auto Latch-up	(Per AEC Q100- 004)	1/6/0	1/6/
ED	E5	AEC Q100-009	3	30	Auto Electrical Distributions	Cpk>1.67	3/90/0	3/90
·				A	Additional Tests			
MSL			-	-	Automotive L3 Powerpad Moisture Sensitivity	Level 3-260C	3/35/0	-
MSL			-	-	Automotive L2 Powerpad Moisture Sensitivity	Level 2-260C	-	3/35

- QBS: Qual By Similarity
- Qual Device TAS5441QPWPRQ1 is qualified at LEVEL3-260C
A1 (PC): Preconditioning:
Performed for THB, Biased HAST, AC, uHAST, TC & PTC samples, as applicable.

Ambient Operating Temperature by Automotive Grade Level:

Grade 0 (or E): -40°C to +150°C Grade 1 (or Q): -40°C to +125°C Grade 2 (or T): -40°C to +105°C Grade 3 (or I) : -40°C to +85°C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

Room/Hot/Cold: HTOL, ED Room/Hot: THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU Room: AC/uHAST

Green/Pb-free Status:

Qualified Pb-Free(SMT) and Green Note (1): Solderability results are from Qual ID# 20090826-9343.

Automotive New Product Qualification Summary (As per AEC-Q100 and JEDEC Guidelines)

Approved 03/17/2015 Qualification Results

		Test Name / Condition	Duration	Qual Device: TP S62090QRGTRQ1	Qual Device: TP S65263QRHBRQ1	Qual Device: TP S62065QD SGRQ1	QBS Process/Package TPS2543QRTE			
Fest Group A - Accelerated En	vironment									
HAST	A2	JESD22- A110	3	77	Biased HAST, 130C/85%RH	96 Hours	1/77/0	1/77/0	1/77/0	3/231/0
AC	A3	JESD22- A102	3	77	Autoclave 121C	96 Hours	1/77/0	1/77/0	1/77/0	3/231/0
TC-BP	A4	MIL-STD883 Method 2011	1	30	Post Temp. Cycle Bond Pull	Wires	1/30/0	1/30/0	1/30/0	1/30/0
TC	A4	JESD22- A104	3	77	Temperature Cycle, -65/150C	500 Cycles	1/77/0	1/77/0	1/77/0	3/231/0
PTC	A5	JESD22- A105	1	45	Power Temperature Cycle, - 40/125C	1000 Cycles	1/45/0	1/45/0	1/45/0	1/45/0
HTSL	A6	JESD22- A103	1	45	High Temp. Storage Bake, 150C	1000 Hours	-	1/45/0	1/45/0	-
HTSL	A6	JESD22- A103	1	45	High Temp. Storage Bake, 175C	500 Hours	1/45/0	-	-	1/45/0
est Group B - Accelerated Life	etime Simi	ulation Test								
HTOL	B1	JESD22- A108	3	77	Life Test, 125C	1000 Hours	1/77/0	1/77/0	1/770	-
HTOL	B1	JESD22- A108	3	77	Life Test, 150C	408 Hours	-	-	-	3/231/0
ELFR	B2	AEC-Q100- 008	3	800	Early Life Failure Rate, 125C	48 Hours	1/800/0	-	-	-
ELFR	B2	AEC-Q100- 008	3	800	Early Life Failure Rate, 150C	24 Hours	-	-	-	3/2400/0
EDR	B3	AEC-Q100- 005	3	77	NVM Endurance, Data Retention, and Operational Life	-	N/A	-	-	-
est Group C - Package Assem	bly Integr	ity Tests								
WBS	C1	AEC-Q100- 001	1	30	Bond Shear (Cpk>1.67)	Wires	1/30/0	-	1/30/0	-
WBP	C2	MIL-STD883 Method 2011	1	30	Bond Pull (Cpk>1.67	Wires	1/30/0	-	1/30/0	-
SD	C3	JESD22- B102	1	15	Surface Mount Solderability	Pb	1/15/0	-	-	-
SD	C3	IESD22	1	15	Surface Mount Solderability	Pb Free	1/15/0	-	-	-
PD	C4	JESD22 B100 and B108	3	10	Physical Dimensions (Cpk>1.67)	-	3/30/0	-	-	-
est Group D - Die Fabrication	Reliability	Tests								
ЕМ	D1	JESD61	-	-	Electromigration	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technolog Requirements
TDDB	D2	JESD35	-	-	Time Dependant Dielectric Breakdown	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technolog Requirements
HCI	D3	JESD60 & 28	-	-	Hot Injection Carrier	-	Completed Per Process Technology Requirements		Completed Per Process Technology Requirements	Completed Per Process Technolog Requirements
NBTI	D4	-	-	-	Negative Bias Temperature Instability	-	Completed Per Process Technology Requirements		Completed Per Process Technology Requirements	Completed Per Process Technolog Requirements
SM	D5	-	-	-	Stress Migration	-	Completed Per Process Technology Requirements		Completed Per Process Technology Requirements	
est Group E - Electrical Verific	ation									
HBM	E2	AEC-Q100- 002	1	3	ESD - HBM	4000 V	-	1/3/0	1/3/0	1/3/0
CDM	E3	AEC-Q100- 011	1	3	ESD - CDM	1500 V	-	1/3/0	1/3/0	1/3/0
LU	E4	AEC-Q100- 004	1	6	Auto Latch-up	(Per AEC Q100- 004)	-	1/6/0	1/6/0	1/6/0
ED	E5	AEC-Q100-	3	30	Electrical Distributions	Cpk>1.67		3/90/0	3/90/0	3/90/0

- QBS: Qual By Similarity - Qual Device TPS62090QRGTRQ1 is qualified at LEVEL2-260C A1 (PC): Preconditioning: Performed for THB, Biased HAST, AC, uHAST & TC samples, as applicable.

Ambient Operating Temperature by Automotive Grade Level: Grade 0 (or E): -40C to +150C Grade 1 (or Q): -40C to +125C Grade 2 (or T): -40C to +105C Grade 3 (or 1): -40C to +85C

C1/C2 (WBS / WBP): Wire Bond Shear & Wire Bond Pull data from eQDB 20140626-106021

C4 (Physical dimensions): Physical Dimensions data from eQDB 20140626-106021

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level): Room/Hot/Cold: HTOL, ED Room/Hot: THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU Room : AC/uHAST

Green/Pb-free Status: Qualified Pb-Free (SMT) and Green

Automotive New Product Qualification Summary

(As per AEC-Q100 and JEDEC Guidelines)

Approved 24-Oct-2018

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Туре	#	Test Spec	Min Lot Qty	SS/ Lot	Test Name / Condition	Duration	Qual Device: TPS61088QRHLQ1	QBS Process Reference: <u>TP S2543QRTE</u>
		Test Group A – Accelerat	ed Envir	ronmen	ıt Stress Tests			
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Automotive Preconditioning	Level 2- 260C	3/AII/0	3/All/0
HAST	A2	JEDEC JESD22-A110	3	77	Biased HAST, 130C/85%RH	96 Hours	1/77/0	3/240/0
AC	A3	JEDEC JESD22-A102	3	77	Autoclave 121C	96 Hours	1/77/0	3/237/0
TC	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle, -65/150C	500 Cycles	3/231/0	3/238/0
TC-BP	A4	MIL-STD883 Method 2011	1	5	Post Temp. Cycle Bond Pull	500 Cycles	1/5/0	1/5/0
PTC	A5	JEDEC JESD22-A105	1	45	Power Temperature Cycle, -40/125C	1000 Cycles	1/45/0	1/50/0
HTSL	A6	JEDEC JESD22-A103	1	45	High Temp. Storage Bake, 150C	1000 Hours	1/45/0	-
HTSL	Aß	JEDEC JESD22-A103	1	45	High Temp. Storage Bake, 175C	500 Hours	-	3/149/0
		Test Group B – Accelerat	ed Lifeti	ime Sin	nulation Tests			
HTOL	B1	JEDEC JESD22-A108	3	77	Life Test, 125C	1000 Hours	1/77/0	-
HTOL	B1	JEDEC JESD22-A108	3	77	Life Test, 150C	408 Hours	-	3/231/0
ELFR	B2	AEC Q100-008	3	800	Early Life Failure Rate, 125C	48 Hours	-	-
ELFR	B2	AEC Q100-008	3	800	Early Life Failure Rate, 150C	24 Hours	-	3/2640/0
EDR	B3	AEC Q100-005	3	77	NVM Endurance, Data Retention, and Operational Life	-	N/A	-

		Test Group C – Pack	age	Asser	nbly Integrity Tests			
WBS	C1	AEC Q100-001	1	30	Bond Shear (Cpk>1.67)	Wires	1/30/0	-
WBP	C2	MIL-STD883 Method 2011	1	30	Bond Pull (Cpk>1.67)	Wires	1/30/0	-
SD	C3	JEDEC JESD22-B102	1	15	Surface Mount Solderability	Pb Free	1/15/0	2/30/0
SD	C3	JEDEC JESD22-B102	1	15	Surface Mount Solderability	Pb Solder	1/15/0	-
PD	C4	JEDEC JESD22-B100 and B108	3	10	Physical Dimensions (Ppk>1.67)		3/90/0	3/90/0
SBS	C5	AEC Q100-010	3	50	Solder Ball Shear (Cpk>1.67)	Post HTSL/Bump	N/A	-
LI	C6	JEDEC JESD22-B105	1	50	Lead Integrity	Leads	N/A	-
		Test Group D – Die	Fabr	ricatio	n Reliability Tests			
EM	D1	JESD61	-	-	Electromigration		Completed Per Process Technology Requirements	-
TDDB	D2	JESD35	-		Time Dependant Dielectric Breakdown	-	Completed Per Process Technology Requirements	-
HCI	D3	JESD60 & 28	-		Hot Injection Carrier	-	Completed Per Process Technology Requirements	-
NBTI	D4	-	-		Negative Bias Temperature Instability		Completed Per Process Technology Requirements	-
SM	D5	-	-	-	Stress Migration	-	Completed Per Process Technology Requirements	-
		Test Group E – E	lectr	ical V	erification Tests			
HBM	E2	AEC Q100-002	1	3	ESD - HBM	2500 V	1/3/0	1/3/0
CDM	E3	AEC Q100-011	1	3	ESD - CDM	1000 V	1/3/0	1/3/0
LU	E4	AEC Q100-004	1	8	Latch-up	(Per AEC Q100- 004)	1/6/0	1/6/0
ED	E5	AEC Q100-009	3	30	Electrical Distributions	Cpk>1.67 Room, Hot, & Cold	3/90/0	3/90/0

- QBS: Qual By Similarity

- Qual Device TPS61088QRHLQ1 is qualified at LEVEL2-260C

A1 (PC): Preconditioning:

Performed for THB, Biased HAST, AC, uHAST, TC & PTC samples, as applicable.

Ambient Operating Temperature by Automotive Grade Level:

Grade 0 (or E): -40°C to +150°C

Grade 1 (or Q): -40°C to +125°C

Grade 2 (or T): -40°C to +105°C

Grade 3 (or I) : -40°C to +85°C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

Room/Hot/Cold : HTOL, ED

Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU Room : AC/uHAST

Green/Pb-free Status:

Qualified Pb-Free(SMT) and Green

Automotive New Product Qualification Summary (As per AEC-Q100 and JEDEC Guidelines)

Approve Date 10-July-2018

Qualification Results Data Displayed as: Number of lots / Total sample size / Total failed

	_		Min				Qual Device:	Qual Device:	QBS Process
Туре	#	Test Spec	Lot	S S/	Test Name / Condition	Duration	TLC6C5724QDAP	TLC6C5712QP	Reference:
.,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,		Tool op oo	Qty	Lot	root number contaition	Daradon	RQ1	WPRQ1	TPS2543QRTE
est Group A	A – Acce	lerated Environment Stress Tests							
PC	A1	JEDEC J-STD-020 JESD22-A113	-	-	Automotive Preconditioning	Level 2-260C			3/765/0
PC	A1	JEDEC J-STD-020 JESD22-A113	-	-	Automotive Preconditioning	Level 3-260C	3/738/0	3/738/0	-
HAST	A2	JEDEC JESD22-A110	1	77	Biased HAST, 130C/85%RH	96 Hours	3/231/0	3/231/0	3/231/0
AC	A3	JEDEC JESD22-A102	1	77	Autoclave 121C	96 Hours	3/231/0	3/231/0	3/231/0
TC	A4	JEDEC JESD22-A104 and Appendix 3	1	77	Temperature Cycle, -65/150C	500 Cycles	3/231/0	3/231/0	3/231/0
TC-BP	A4 A4	MIL-STD883 Method 2011	1	5	Post Temp. Cycle Bond Pull	per MIL-STD 883 Method 2011	1/5/0	-	1/5/0
PTC	A5	JEDEC JESD22-A105	1	45	Power Temperature Cycle, -40/125C	1000 Cycles	1/45/0	-	1/45/0
HTSL	A6	JEDEC JESD22-A103	1	77	High Temp. Storage Bake, 150C	1000 Hours	1/77/0	-	-
HTSL	A6	JEDEC JESD22-A103	1	45	High Temp. Storage Bake, 175C	500 Hours	-	1/45/0	3/135/0
est Group	B – Acce	lerated Lifetime Simulation Tests							
HTOL	B1	JEDEC JESD22-A108	1	77	Life Test, 150C	408 Hours	1/77/0	3/231/0	
HTOL	B1	JEDEC JESD22-A108	3	77	Life Test, 125C	1000 Hours	-	-	3/231/0
ELFR	B2	AEC Q100-008	3	800	Early Life Failure Rate, 150C	24 Hours	-	3/2400/0	3/2240/0
ELFR	B2	AEC Q100-008	3	800	Early Life Failure Rate, 1350	48 Hours	-	5/2400/0	3/2240/0
est Group (age Assembly Integrity Tests	5	000	Early Elle Failure Rate, 1250	40110013			
			4	20	Read Chass (Oals 4.07)	146	2/00/0		
WBS	C1	AEC Q100-001	1	30	Bond Shear (Cpk>1.67)	Wires	3/90/0	-	-
WBP	C2	MIL-STD883 Method 2011	1	30	Bond Pull (Cpk>1.67)	Wires	3/90/0	-	-
SD	C3	JEDEC JESD22-B102	1	15	Surface Mount Solderability >95% Lead Coverage	8 Hours Steam Age, Pb	-	-	1/15/0
SD	C3	JEDEC JESD22-B102	1	15	Surface Mount Solderability >95% Lead Coverage	8 Hours Steam Age, Pb Free	1/22/0	-	1/15/0
PD	C4	JEDEC JESD22-B100 and B108	3	10	Physical Dimensions (Cpk>1.67)	-	3/30/0	-	3/30/0
st Group D) – Die Fa	abrication Reliability Tests					Completed Per	Completed Per	Completed Pe
EM	D1	JESD61	-	-	Electromigration	-	Process Technology Requirements	Process Technology Requirements	Process Technology Requirements
TDDB	D2	JESD35	-	-	Time Dependent Dielectric Breakdown	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
HCI	D3	JESD60 & 28	-	-	Hot Injection Carrier	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Pe Process Technology Requirements
NBTI	D4	-	-	-	Negative Bias Temperature Instability	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Pe Process Technology Requirements
SM	D5	-	-	-	Stress Migration	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Pe Process Technology Requirements
st Group E	E – Electr	ical Verification Tests							
HBM	E2	AEC Q100-002	1	3	ESD - HBM	2000 V	1/3/0	1/3/0	1/3/0
HBM	E2	AEC Q100-002	1	3	ESD - HBM	4000 V	-	1/3/0	-
CDM	E3	AEC Q100-011	1	3	ESD - CDM	500 V	1/3/0	-	-
CDM	E3	AEC Q100-011	1	3	ESD - CDM	750 V	1/3/0	1/3/0	
CDM	E3	AEC Q100-011	1	3	ESD - CDM	1000 V	-	1/3/0	1/3/0
LU	E4	AEC Q100-004	1	6	Latch-up	(Per AEC Q100-004)	1/6/0	1/6/0	1/6/0
1 10 1	E4	AEG @100-004	1	U	Laton-up	(Per AEC Q100-004) Cpk>1.67 Room,	1/0/0	1/0/0	1/0/0

A1 (PC): Preconditioning: Performed for THB, Biased HAST, AC, uHAST &TC samples, as applicable.

Junction Operating Temperature by Automotive Grade Level: Grade 0 (or E): -40°C to +150°C Grade 1 (or Q): -40°C to +125°C Grade 2 (or T): -40°C to +105°C Grade 3 (or I): -40°C to +85°C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level): Room/Hot/Cold : HTOL, ED Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU Room : AC/uHAST

Green/Pb-free Status: Qualified Pb-Free (SMT) and Green

For questions regarding this notice, e-mails can be sent to the contact below or your local Field Sales Representative.

Location	E-Mail				
WW Change Management Team	PCN ww admin team@list.ti.com				

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